

2SB1322

Silicon PNP epitaxial planar type

For low frequency power amplification

Complementary to 2SD1994

■ Features

- Allowing supply with the radial taping

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	-30	V
Collector-emitter voltage (Base open)	V_{CEO}	-25	V
Emitter-base voltage (Collector open)	V_{EBO}	-5	V
Collector current	I_{C}	-1	A
Peak collector current	I_{CP}	-1.5	A
Collector power dissipation	P_{C}	1	W
Junction temperature	T_{j}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Package

- Code
MT-2-A1
- Pin Name
 1. Emitter
 2. Collector
 3. Base

■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_{\text{C}} = -10 \mu\text{A}, I_{\text{E}} = 0$	-30			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_{\text{C}} = -2 \text{ mA}, I_{\text{B}} = 0$	-25			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_{\text{E}} = -10 \mu\text{A}, I_{\text{C}} = 0$	-5			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{\text{CB}} = -20 \text{ V}, I_{\text{E}} = 0$			-0.1	μA
Forward current transfer ratio *1	h_{FE1} *2	$V_{\text{CE}} = -10 \text{ V}, I_{\text{C}} = -500 \text{ mA}$	85		340	—
	h_{FE2}	$V_{\text{CE}} = -5 \text{ V}, I_{\text{C}} = -1 \text{ mA}$	50			—
Collector-emitter saturation voltage *1	$V_{\text{CE(sat)}}$	$I_{\text{C}} = -500 \text{ mA}, I_{\text{B}} = -50 \text{ mA}$			-0.4	V
Base-emitter saturation voltage *1	$V_{\text{BE(sat)}}$	$I_{\text{C}} = -500 \text{ mA}, I_{\text{B}} = -50 \text{ mA}$			-1.2	V
Transition frequency	f_{T}	$V_{\text{CB}} = -10 \text{ V}, I_{\text{E}} = 50 \text{ mA}, f = 200 \text{ MHz}$		200		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{\text{CB}} = -10 \text{ V}, I_{\text{E}} = 0, f = 1 \text{ MHz}$		20	30	pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

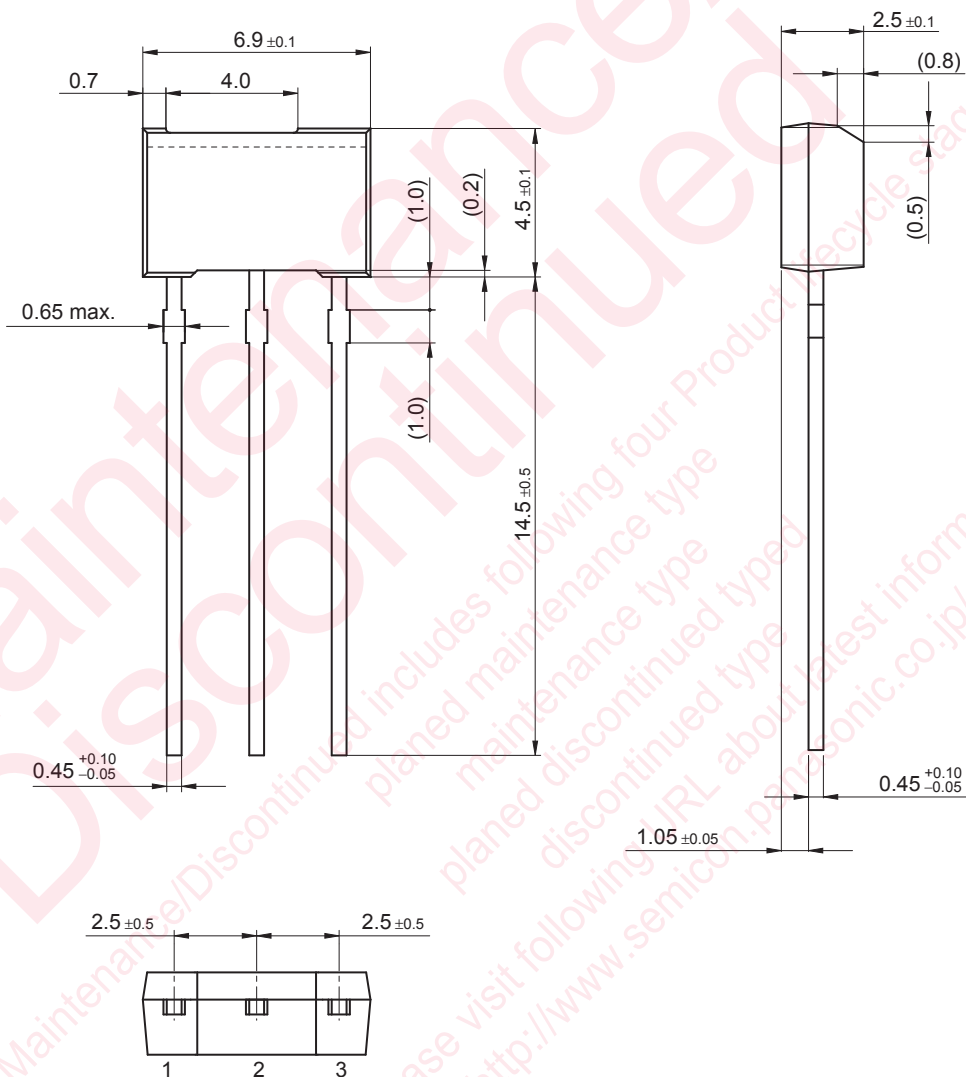
2. *1: Pulse measurement

*2: Rank classification

Rank	Q	R	S
h_{FE1}	85 to 170	120 to 240	170 to 340

MT-2-A1

Unit: mm



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